

# Thyristor

$$V_{RRM} = 1600 \text{ V}$$

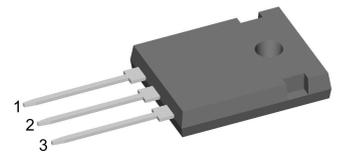
$$I_{TAV} = 80 \text{ A}$$

$$V_T = 1.43 \text{ V}$$

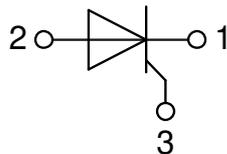
## Single Thyristor

Part number

**CMA80E1600HB**



Backside: anode



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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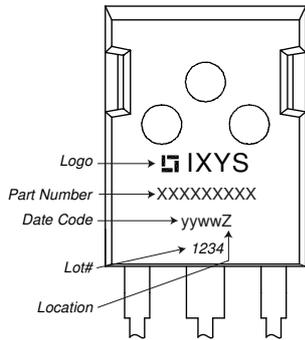


Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$		10	$\mu A$	
		$V_{R/D} = 1600 V$	$T_{VJ} = 125^{\circ}C$		3	mA	
$V_T$	forward voltage drop	$I_T = 80 A$	$T_{VJ} = 25^{\circ}C$		1.47	V	
		$I_T = 160 A$			1.90	V	
		$I_T = 80 A$	$T_{VJ} = 125^{\circ}C$		1.43	V	
		$I_T = 160 A$			1.93	V	
$I_{TAV}$	average forward current	$T_C = 115^{\circ}C$	$T_{VJ} = 150^{\circ}C$		80	A	
$I_{T(RMS)}$	RMS forward current	180° sine			126	A	
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.90	V	
$r_T$	slope resistance				6.4	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.2	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		620	W	
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		720	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		780	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		610	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		660	A	
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		2.59	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		2.53	kA <sup>2</sup> s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		1.86	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1.81	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		32	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
$P_{GAV}$	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 240 A$		150	A/ $\mu s$	
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 80 A$		500	A/ $\mu s$	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 125^{\circ}C$		1000	V/ $\mu s$	
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.4	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		80	mA	
			$T_{VJ} = -40^{\circ}C$		200	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V	
$I_{GD}$	gate non-trigger current				5	mA	
$I_L$	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		450	mA	
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$					
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$	
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$					
$t_q$	turn-off time	$V_R = 100 V; I_T = 80 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 15 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	$\mu s$	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

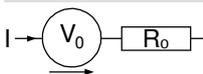
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 80 = Current Rating [A]
- E = Single Thyristor
- 1600 = Reverse Voltage [V]
- HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CMA80E1600HB	CMA80E1600HB	Tube	30	513206

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 150^{\circ}C$

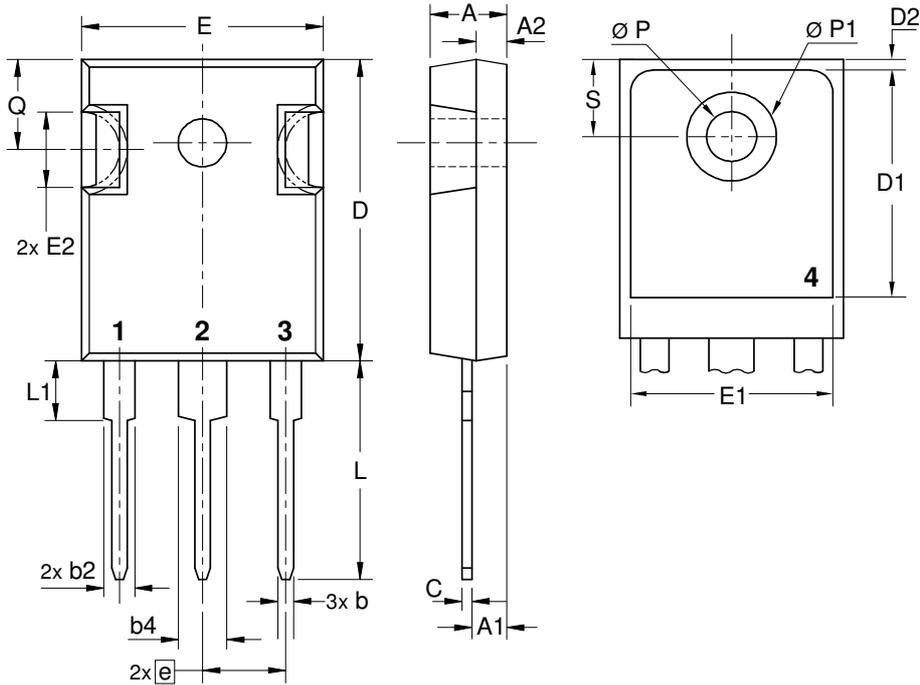


**Thyristor**

$V_{0\ max}$	threshold voltage	0.9	V
$R_{0\ max}$	slope resistance *	3.9	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

